

# FCP36N60N / FCPF36N60NT

## N 沟道 SupreMOS® MOSFET

600 V, 36 A, 90 mΩ

### 特性

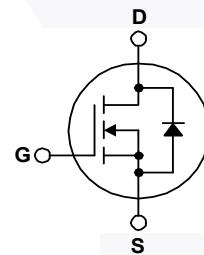
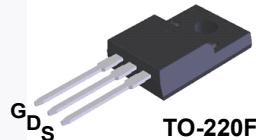
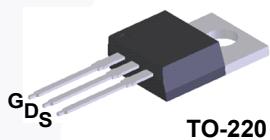
- $R_{DS(on)} = 81 \text{ mΩ}$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 18 \text{ A}$
- 超低栅极电荷 (典型值  $Q_g = 86 \text{ nC}$ )
- 低有效输出电容 (典型值  $C_{oss(\text{eff.})} = 361 \text{ pF}$ )
- 100% 经过雪崩测试
- 符合 RoHS 标准

### 应用

- 太阳能逆变器
- AC-DC 电源

### 说明

SupreMOS® MOSFET 是飞兆半导体的下一代高压超级结 (SJ) 技术，该技术采用区别于传统 SJ MOSFET 产品的深沟槽填充工艺。这项先进技术和精密的工艺控制提供了最低的  $R_{sp(on)}$  (导通电阻规格)，卓越的开关性能和耐用性。SupreMOS MOSFET 产品非常适合高频开关电源转换器应用，如功率因数校正 (PFC)、服务器 / 电信电源、平板电视电源、ATX 电源及工业电源应用。



绝对最大额定值  $T_C = 25^\circ\text{C}$  除非另有说明。

符号	参数		FCP36N60N	FCPF36N60NT	单位
$V_{DSS}$	漏极—源极电压		600		V
$V_{GSS}$	栅极—源极电压		$\pm 30$		V
$I_D$	漏极电流	- 连续 ( $T_C = 25^\circ\text{C}$ )	36	36*	A
		- 连续 ( $T_C = 100^\circ\text{C}$ )	22.7	22.7*	
$I_{DM}$	漏极电流	- 脉冲 (注 1)	108	108*	A
$E_{AS}$	单脉冲雪崩能量	(注 2)	1800		mJ
$I_{AR}$	雪崩电流	(注 1)	12		A
$E_{AR}$	重复雪崩能量	(注 1)	3.12		mJ
$dv/dt$	MOSFET $dv/dt$		100		V/ns
	峰值二极管恢复 $dv/dt$	(注 3)	20		
$P_D$	功耗	( $T_C = 25^\circ\text{C}$ )	312		W
		- 降低至 $25^\circ\text{C}$ 以上	2.6		W/°C
$T_J, T_{STG}$	工作和存储温度范围		-55 to +150		°C
$T_L$	用于焊接的最高引脚温度， 距离外壳 1/8", 持续 5 秒		300		°C

\* 漏极电流受限于最大结温

### 热性能

符号	参数	FCP36N60N	FCPF36N60NT	单位
$R_{θJC}$	结至外壳热阻最大值	0.4	3.5	°C/W
$R_{θCS}$	外壳与散热片之间的热阻典型值	0.5	0.5	
$R_{θJA}$	结至环境热阻最大值	62.5	62.5	

## 封装标识与定购信息

器件编号	顶标	封装	包装方法	卷尺寸	带宽	数量
FCP36N60N	FCP36N60N	TO-220	塑料管	不适用	不适用	50 个
FCPF36N60NT	FCPF36N60NT	TO-220F	塑料管	不适用	不适用	50 个

**电气特性**  $T_C = 25^\circ\text{C}$  除非另有说明。

符号	参数	测试条件	最小值	典型值	最大值	单位
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## 关断特性

$\text{BV}_{\text{DSS}}$	漏极 - 源极击穿电压	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}, T_C = 25^\circ\text{C}$	600	-	-	V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	击穿电压温度系数	$I_D = 1 \text{ mA}$ , 温度参考 $25^\circ\text{C}$	-	0.7	-	$\text{V}/^\circ\text{C}$
$I_{\text{DSS}}$	零栅极电压漏极电流	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	10	$\mu\text{A}$
		$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_C = 125^\circ\text{C}$	-	-	100	
$I_{\text{GSS}}$	栅极 - 体漏电流	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	$\pm 100$	nA

## 导通特性

$V_{GS(\text{th})}$	栅极阈值电压	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	2.0	-	4.0	V
$R_{DS(\text{on})}$	漏极至源极静态导通电阻	$V_{GS} = 10 \text{ V}, I_D = 18 \text{ A}$	-	81	90	$\text{m}\Omega$
$g_{FS}$	正向跨导	$V_{DS} = 20 \text{ V}, I_D = 18 \text{ A}$	-	41	-	S

## 动态特性

$C_{iss}$	输入电容	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	3595	4785	pF
$C_{oss}$	输出电容		-	149	200	pF
$C_{rss}$	反向传输电容		-	4	6	pF
$C_{oss}$	输出电容	$V_{DS} = 380 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	80	-	pF
$C_{oss(\text{eff.})}$	有效输出电容	$V_{DS} = 0 \text{ V to } 380 \text{ V}, V_{GS} = 0 \text{ V}$	-	361	-	pF
$Q_{g(\text{tot})}$	10 V 的栅极电荷总量	$V_{DS} = 380 \text{ V}, I_D = 18 \text{ A}, V_{GS} = 10 \text{ V}$	-	86	112	nC
$Q_{gs}$	栅极 - 源极栅极电荷	(说明 4)	-	15.4	-	nC
$Q_{gd}$	栅极 - 漏极 “米勒” 电荷		-	26.4	-	nC
ESR	等效串联电阻	$f = 1 \text{ MHz}$	-	1	-	$\Omega$

## 开关特性

$t_{d(on)}$	导通延迟时间	$V_{DD} = 380 \text{ V}, I_D = 18 \text{ A}, V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$	-	23	56	ns
$t_r$	开通上升时间		-	22	54	ns
$t_{d(off)}$	关断延迟时间		-	94	198	ns
$t_f$	关断下降时间		-	4	18	ns

## 漏极 - 源极二极管特性

$I_S$	漏极 - 源极二极管最大正向连续电流	-	-	18	A
$I_{SM}$	漏极 - 源极二极管最大正向脉冲电流	-	-	108	A
$V_{SD}$	漏极 - 源极二极管正向电压	$V_{GS} = 0 \text{ V}, I_{SD} = 18 \text{ A}$	-	-	1.2
$t_{rr}$	反向恢复时间	$V_{GS} = 0 \text{ V}, I_{SD} = 18 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$	-	574	-
$Q_{rr}$	反向恢复电荷		-	10	$\mu\text{C}$

### 注意:

- 重复额定值: 脉冲宽度受限于最大结温。
- $I_{AS} = 12 \text{ A}, R_G = 25 \Omega$ , 启动  $T_J = 25^\circ\text{C}$ 。
- $I_{SD} \leq 36 \text{ A}, di/dt \leq 200 \text{ A}/\mu\text{s}, V_{DD} = 380 \text{ V}$ , 启动  $T_J = 25^\circ\text{C}$ 。
- 本质上独立于工作温度的典型特性。

## 典型性能特征

图 1. 导通区域特性

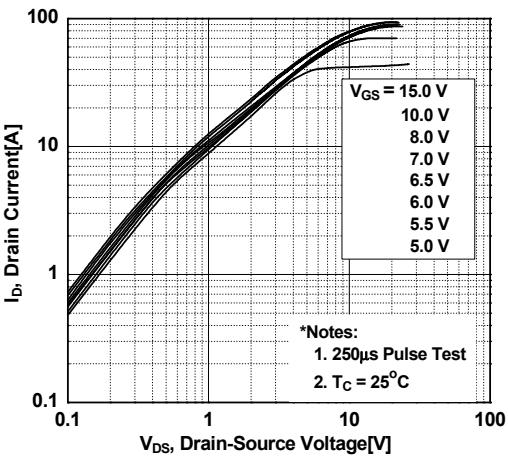


图 2. 传输特性

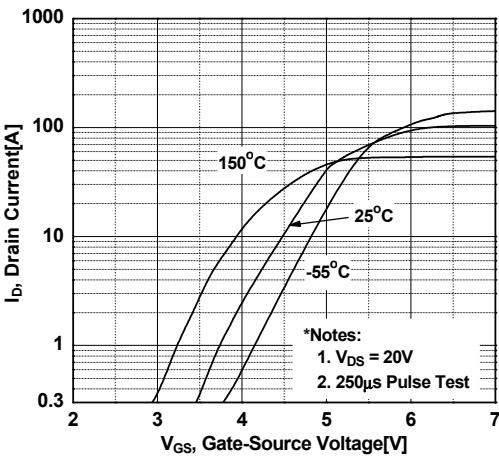


图 3. 导通电阻变化 vs. 漏极电流和栅极电压

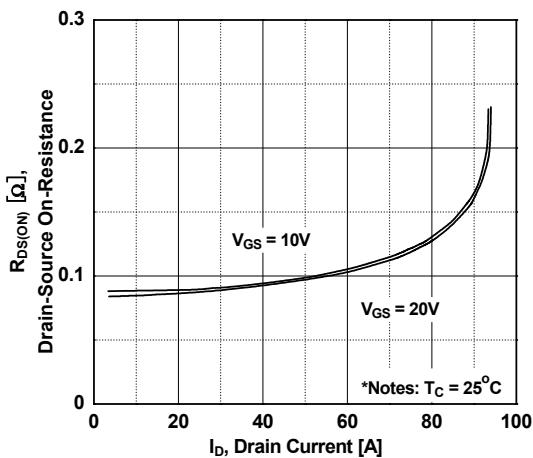


图 4. 体二极管正向电压变化 vs. 源极电流和温度

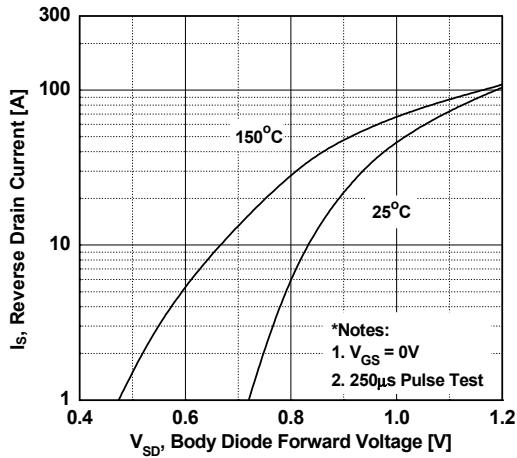


图 5. 电容特性

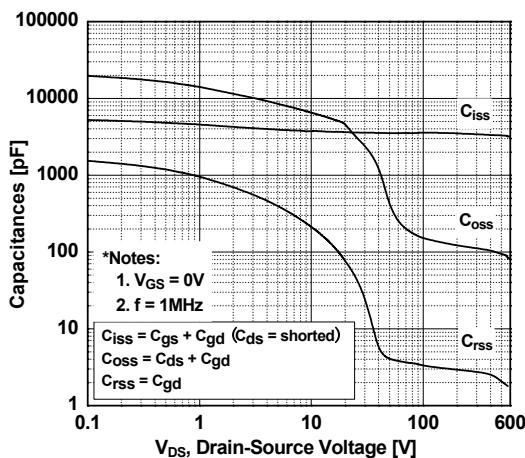
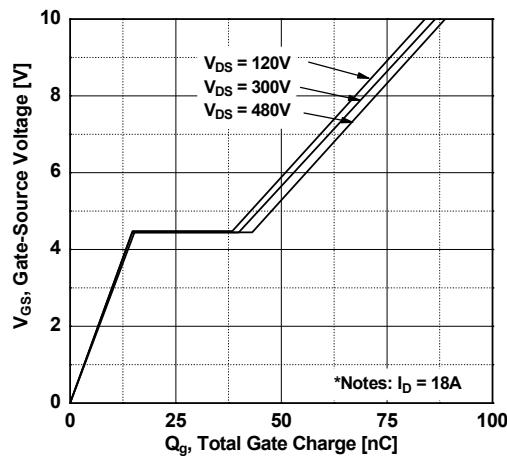


图 6. 栅极电荷特性



## 典型性能特征 (接上页)

图 7. 击穿电压变化 vs. 温度

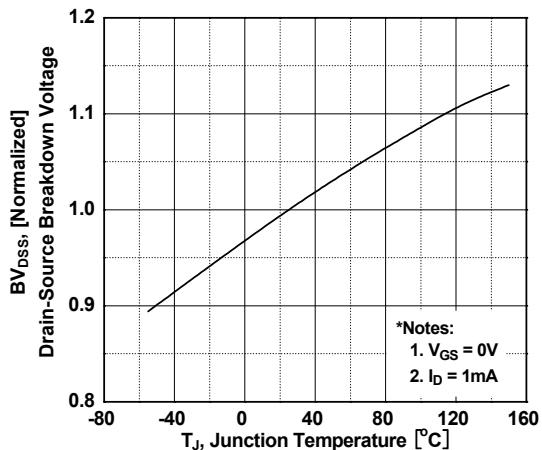


图 9. 最大安全工作区用于 FCP36N60N

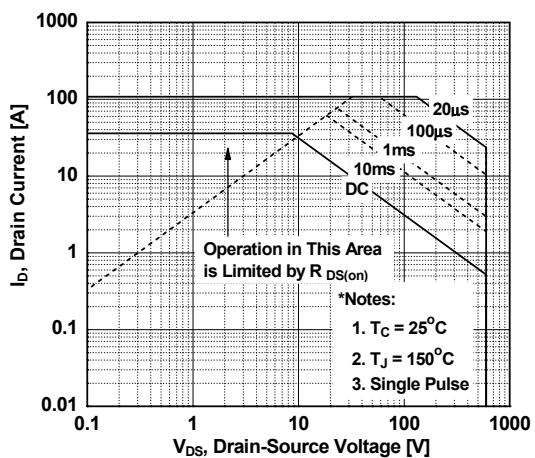


图 11. 最大漏极电流与壳体温度

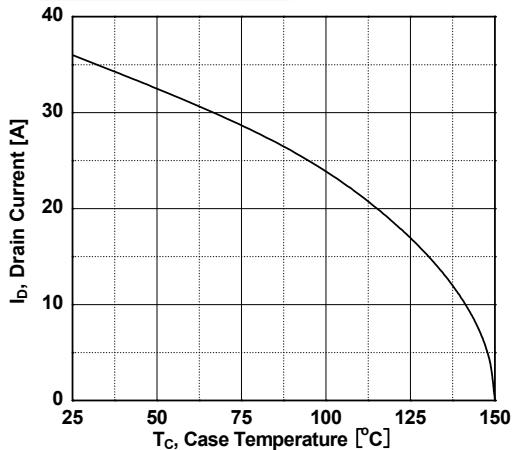


图 8. 导通电阻变化 vs. 温度

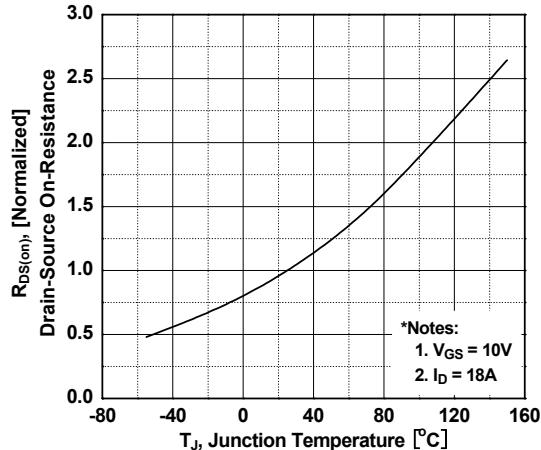
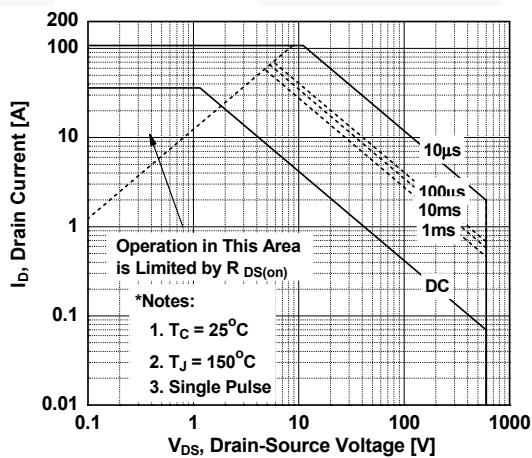


图 10. 最大安全操作区用于 FCPF36N60NT



## 典型性能特征 (接上页)

图 12. 瞬态热响应曲线用于 FCP36N60N

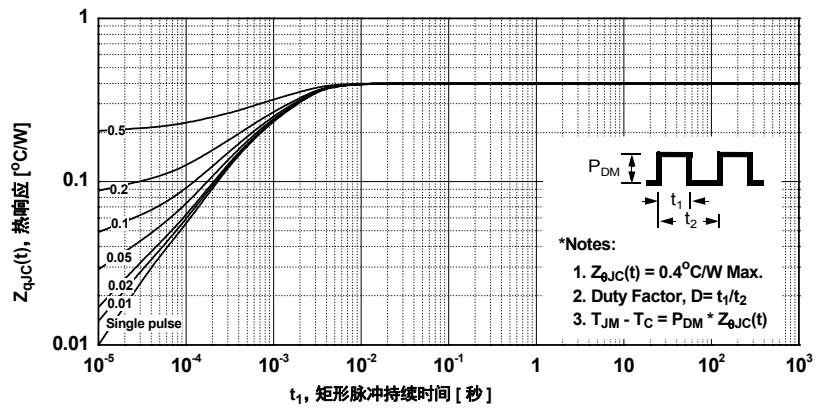
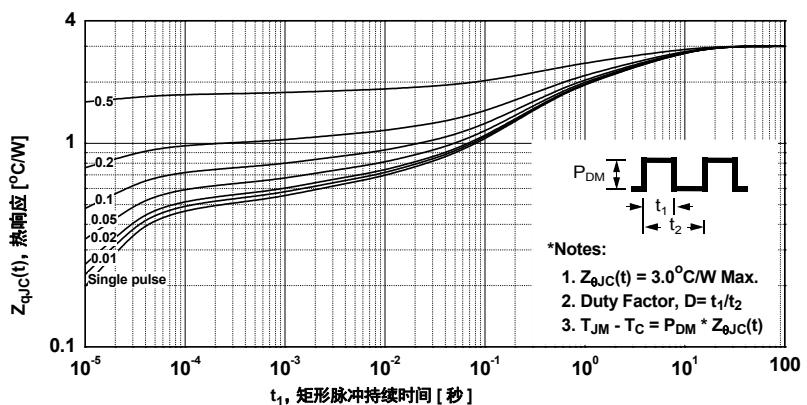


图 13. 瞬态热响应曲线用于 FCPF36N60NT



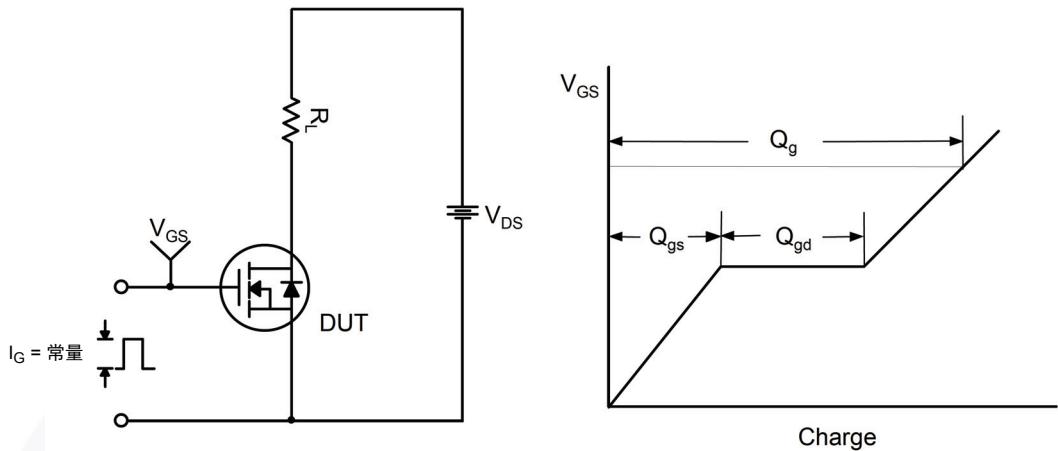


图 14. 栅极电荷测试电路与波形

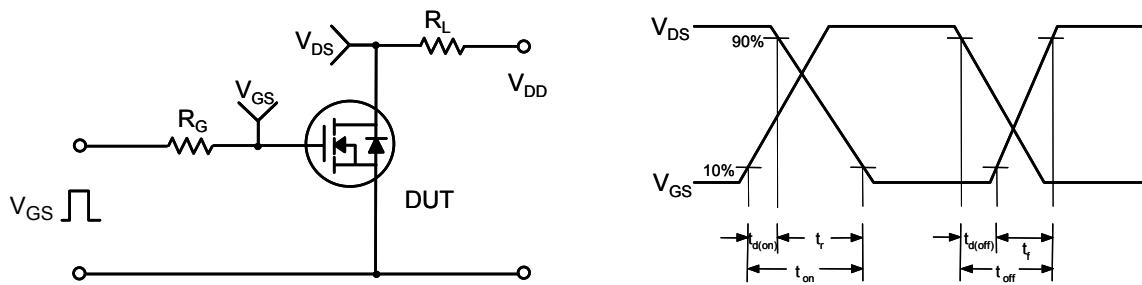


图 15. 阻性开关测试电路与波形

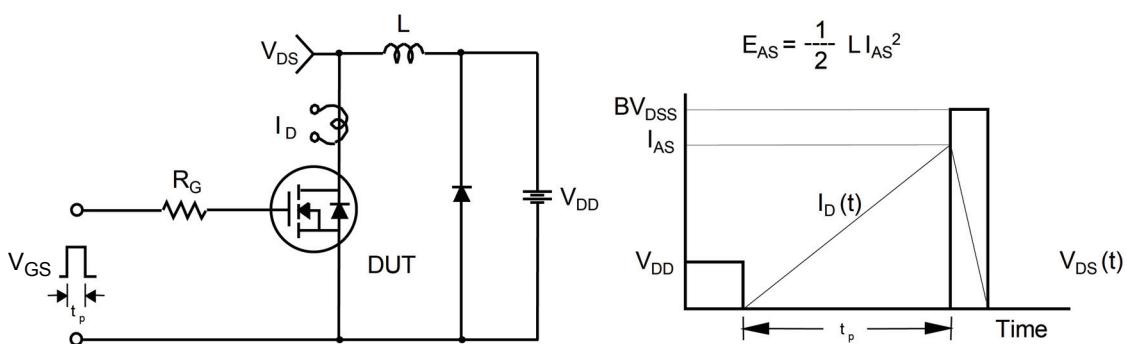


图 16. 非箝位电感开关测试电路与波形

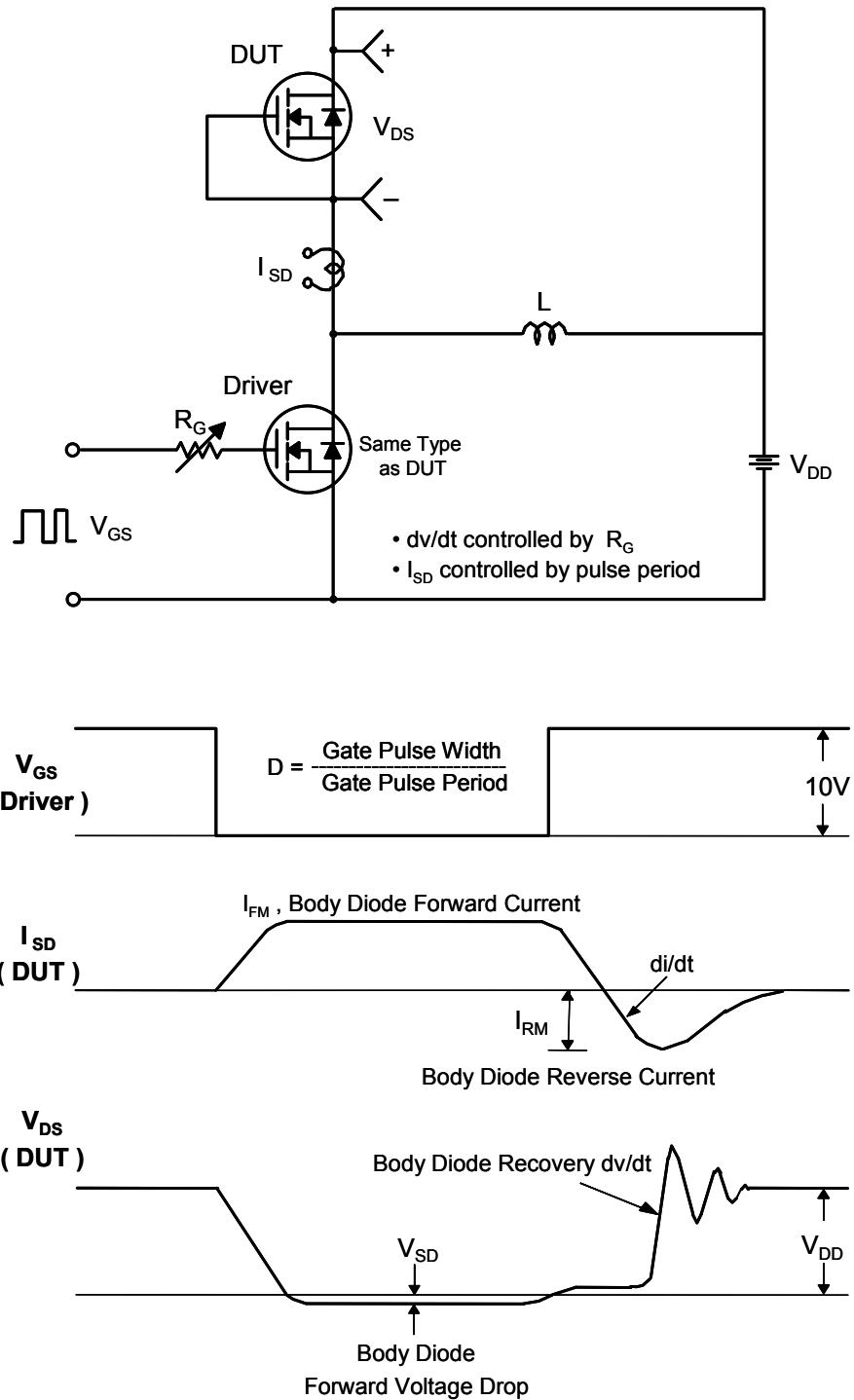


图 17. 二极管恢复  $dv/dt$  峰值测试电路与波形

### 机械尺寸

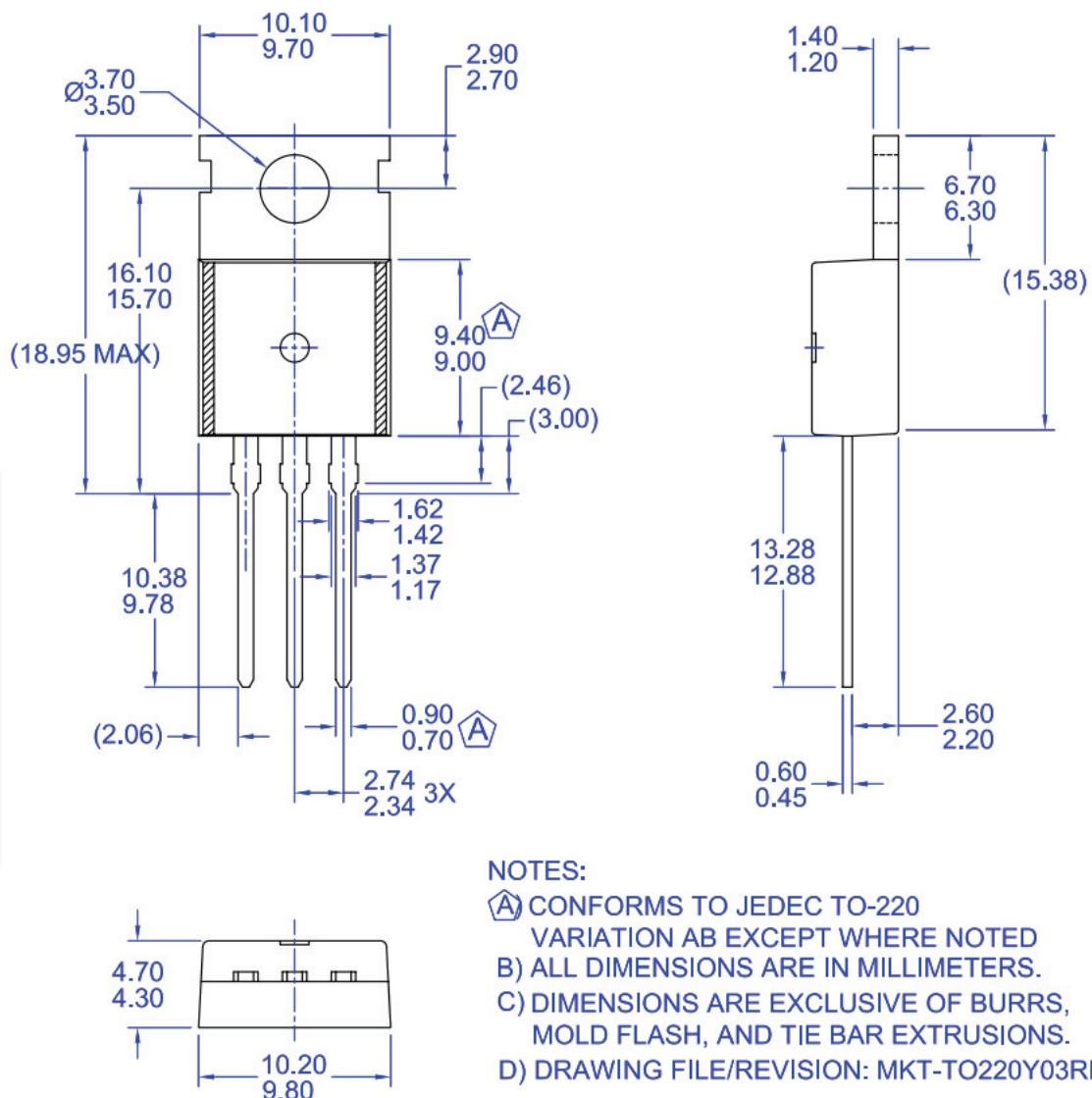


图 18. TO220, 模塑, 3 引脚, 非 Jedec 变体 AB

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### 机械尺寸

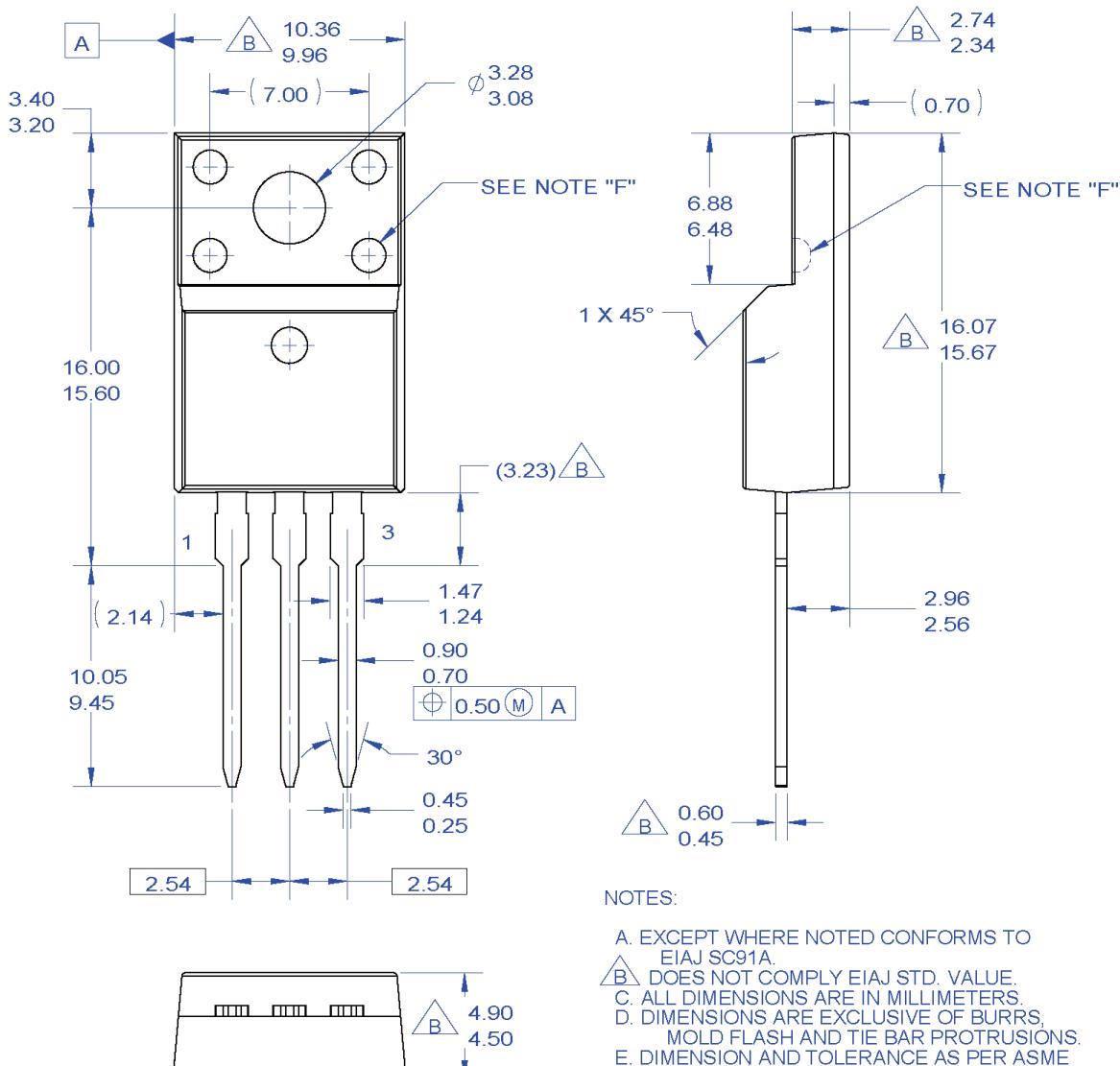


图 19. TO220, 模塑, 3 引脚, 全封装, EIAJ SC91, 直引脚

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